Notice of Allowability	Application No.	Applicant(s)	
	10/620,430	INOUE ET AL.	
	Examiner	Art Unit	
	Belur V Keshavan	2825	
The MAILING DATE of this communication appears on the cover sheet with the correspondence address All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.			
1. This communication is responsive to 10/27/2004.			
2. The allowed claim(s) is/are <u>1-7</u> .			
3. ☑ The drawings filed on 17 July 2003 are accepted by the Examiner.			
 4. Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b)			
 Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 17/07/2003 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material 	5. Notice of Informal F 6. Interview Summary Paper No./Mail Da 7. Examiner's Amendr 8. Examiner's Stateme 9. Other	(PTO-413), te ment/Comment	

DETAILED ACTION

Allowable Subject Matter

Claims 1-7 are allowed.

An Examiner's Statement Of Reasons For Allowance

The following is an examiner's statement of reasons for allowance:

The invention is related to a method of fabrication of aluminum gallium nitride semiconductor device. The primary reason for the allowability of claims 1-7 is the inclusion therein, in combination as currently claimed of the limitation of fabricating aluminum gallium nitride semiconductor device comprising inter alia the following limitations: Forming a protection film having an opening and containing silicon on a first semiconductor layer of aluminum gallium nitride; and heat treating the first semiconductor layer in an oxidizing ambient at a temperature range adjusted to be at 950 °C or more and 1050 °C or less. The limitations found in claims 1-7 are neither disclosed nor taught by the prior art of record, alone or in combination.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Contact Information

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Belur V Keshavan whose telephone number is 571-272-1894. The examiner can normally be reached on 8-4:30 Monday to Friday.

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew S Smith can be reached on 571-272-1907. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

BVK. November 17, 2004. Belur V. Keshavan. Examiner. Art Unit 2825. Page 3

MATTHEW SMITH SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 2800

Please note: The temperature varye of claim 1; s read to be 950° < T < 1050°C.